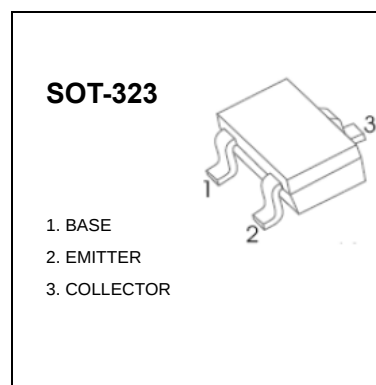


Plastic-Encapsulate Transistors

TRANSISTOR (PNP)

FEATURES

- Ideally suited for automatic insertion
- For Switching and AF Amplifier Applications



Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Collector Base Voltage	BC856W $-V_{CBO}$	80	V
	BC857W, BC860W $-V_{CBO}$	50	V
	BC858W, BC859W $-V_{CBO}$	30	V
Collector Emitter Voltage	BC856W $-V_{CEO}$	65	V
	BC857W, BC860W $-V_{CEO}$	45	V
	BC858W, BC859W $-V_{CEO}$	30	V
Emitter Base Voltage	$-V_{EBO}$	5	V
Collector Current	$-I_C$	100	mA
Peak Collector Current	$-I_{CM}$	200	mA
Power Dissipation	P_{tot}	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 65 to + 150	$^\circ\text{C}$

MARKING CODE

TYPE	856AW	856BW	856CW	857AW	857BW	857CW	858AW	858BW	858CW
MARKING	3A	3B	3C	3E	3F	3G	3J	3K	3L
TYPE	859AW	859BW	859CW	860AW	860BW	860CW			
MARKING	4A	4B	4C	4E	4F	4G			

Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min.	Max.	Unit
DC Current Gain at $-V_{CE} = 5\text{ V}$, $-I_C = 2\text{ mA}$ Current Gain Group A B C	h_{FE} h_{FE} h_{FE}	110 200 420	220 450 800	- - -
Collector Base Cutoff Current at $-V_{CB} = 30\text{ V}$	$-I_{CBO}$	-	15	nA
Collector Base Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$ BC856W BC857W, BC860W BC858W, BC859W	$-V_{(BR)CBO}$ $-V_{(BR)CBO}$ $-V_{(BR)CBO}$	80 50 30	- - -	V V V
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ }\mu\text{A}$ BC856W BC857W, BC860W BC858W, BC859W	$-V_{(BR)CES}$ $-V_{(BR)CES}$ $-V_{(BR)CES}$	80 50 30	- - -	V V V
Collector Emitter Breakdown Voltage at $-I_C = 10\text{ mA}$ BC856W BC857W, BC860W BC858W, BC859W	$-V_{(BR)CEO}$ $-V_{(BR)CEO}$ $-V_{(BR)CEO}$	65 45 30	- - -	V V V
Emitter Base Breakdown Voltage at $-I_E = 1\text{ }\mu\text{A}$	$-V_{(BR)EBO}$	5	-	V
Collector Emitter Saturation Voltage at $-I_C = 10\text{ mA}$, $-I_B = 0.5\text{ mA}$ at $-I_C = 100\text{ mA}$, $-I_B = 5\text{ mA}$	$-V_{CE(sat)}$ $-V_{CE(sat)}$	- -	0.3 0.65	V V
Base Emitter On Voltage at $-I_C = 2\text{ mA}$, $-V_{CE} = 5\text{ V}$ at $-I_C = 10\text{ mA}$, $-V_{CE} = 5\text{ V}$	$-V_{BE(on)}$ $-V_{BE(on)}$	- -	0.75 0.82	V V
Current Gain Bandwidth Product at $-V_{CE} = 5\text{ V}$, $-I_C = 10\text{ mA}$, $f = 100\text{ MHz}$	f_T	100	-	MHz
Output Capacitance at $-V_{CB} = 10\text{ V}$, $f = 1\text{ MHz}$	C_{ob}	-	6	pF



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BC856W-BC860W



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